TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

2SK3497

High Power Amplifier Application

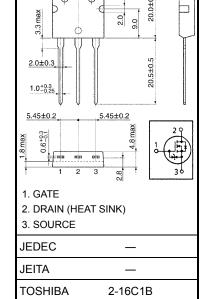
Unit: mm

ø3.2±0.2

- High breakdown voltage: VDSS = 180V
- Complementary to 2SJ618

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	180	V	
Gate-source voltage		V_{GSS}	±12	V	
Drain current	DC (Note 1)	ID	10	Α	
	Pulse (Note 1)	I _{DP}	30	Α	
Drain power dissipation (Tc = 25°C)		P_{D}	130	W	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	



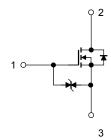
15.9 max

Weight: 4.6 g (typ.)

- Note 1: Ensure that the channel temperature does not exceed 150°C.
- Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit	
Thermal resistance, channel to case	R _{th (ch-c)}	0.96	°C/W	
Thermal resistance, channel to ambient	R _{th (ch-a)}	50	°C/W	

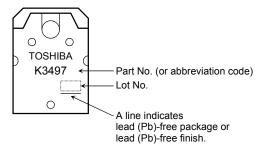


Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V _{GS} = ±12 V, V _{DS} = 0 V	_	_	10	μΑ
Drain cut-off current	I _{DSS}	V _{DS} = 180V, V _{GS} = 0 V	_	_	100	μA
Drain-source breakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	180	_	_	٧
Gate threshold voltage	V_{th}	V _{DS} = 10 V, I _D = 1 mA	1.1	_	2.1	V
Drain-source saturation voltage	V _{DS} (ON)	V _{GS} = 7 V, I _D = 5 A	_	_	0.75	V
Forward transfer admittance	Y _{fs}	V _{DS} = 10 V, I _D = 5 A	6.0	12.0	_	S
Input capacitance	C _{iss}		_	2400	_	
Reverse transfer capacitance	C _{rss}	V _{DS} = 30 V, V _{GS} = 0 V, f = 1 MHz	_	220	_	pF
Output capacitance	Coss			30	_	

This transistor is an electrostatic-sensitive device. Please handle with caution.

Marking



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20070701-EN

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